wiring contacted to the most inner layer of said protective diode is contacted to said diffusion region.

7. (Amended) A semiconductor device comprising:

an insulating gate field effect transistor comprising a plurality of transistor cells which are arranged in a semiconductor layer and connected in parallel; and

a protective diode connected between a gate and a source of said insulating gate field effect transistor to break down an input of a constant voltage or more applied between said gate and said source,

wherein said protective diode is formed as a bidirectional diode in which one or more ring-shaped p-type layers and one or more ring-shaped n-type layers are alternately laminated in a height direction three or more layers on an insulating layer at a peripheral portion of said transistor cells, ring-shaped metal films contacting with the bottom layer and the top layer of said p-type layers or said n-type layers are formed respectively, and each of said metal films is successively formed with either of a source wiring or a gate electrode pad consisting of a metal film, respectively.

A marked-up copy of the amended claims is attached as required under 37 C.F.R. § 1.121.

REMARKS

The following remarks are fully and completely responsive to the Office Action dated October 24, 2002. Claims 1-7 are pending in this application. In the outstanding Office Action, claims 1-7 were rejected under 35 U.S.C. § 103(a) (three different